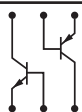


CMXT3946

**SURFACE MOUNT
DUAL COMPLEMENTARY
SILICON TRANSISTORS**



SOT-26 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT3946 type is a dual complementary silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, and designed for small signal general purpose and switching applications.

MARKING CODE: X46

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	NPN	PNP	UNITS
V_{CBO}	60	40	V
V_{CEO}	40	40	V
V_{EBO}	6.0	5.0	V
I_C	200		mA
P_D	350		mW
T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
θ_{JA}	357		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$	-	50	-	50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	40	-	V
BV_{CEO}	$I_C=1.0\text{mA}$	40	-	40	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	0.20	-	0.25	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.30	-	0.40	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.85	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.95	-	0.95	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	40	-	60	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	70	-	80	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100	300	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	60	-	60	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	30	-	30	-	
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300	-	250	-	MHz
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$	-	4.0	-	4.5	pF
C_{ib}	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	12	-	12	pF
h_{ie}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	1.0	10	2.0	12	k Ω
h_{re}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	0.5	8.0	0.1	10	$\times 10^{-4}$

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CMXT3946

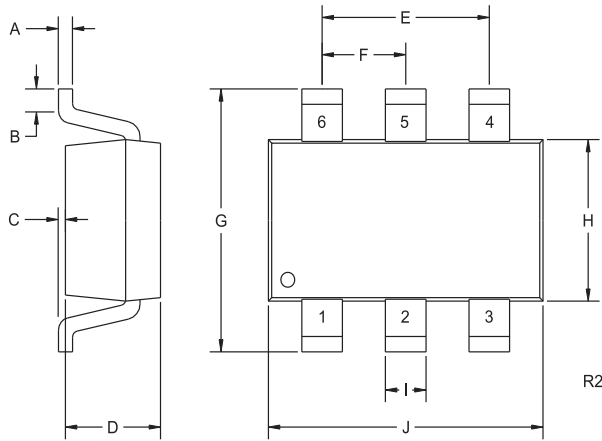
**SURFACE MOUNT
DUAL COMPLEMENTARY
SILICON TRANSISTORS**



ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

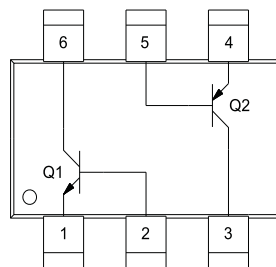
SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
h_{fe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	100	400	100	400	
h_{oe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	1.0	40	3.0	60	μS
NF	$V_{CE}=5.0\text{V}$, $I_C=100\mu\text{A}$, $R_S=1.0\text{k}\Omega$, $f=10\text{Hz}$ to 15.7kHz	-	5.0	-	4.0	dB
t_d	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_r	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$	-	35	-	35	ns
t_s	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$	-	200	-	225	ns
t_f	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$	-	50	-	75	ns

SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS		MIN	MAX
	INCHES	MILLIMETERS		
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	-	0.016	-	0.41
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)



LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X46

R4 (16-March 2020)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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